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(54) Title: <u>AN IMPROVED METHOD FOR MANUFACTURING CRYSTALLINE LAYERED SODIUM DISILICATE</u>					
(57) Abstract <p>The present invention relates to an improved method for manufacturing a crystalline layered sodium disilicate and more particularly, to the improved method for manufacturing the crystalline layered sodium disilicate comprising the steps including the preparation of granules in a certain ratio of anhydrous sodium silicate cullet, a starting material, in the presence of some binders such as water and an aqueous solution of sodium silicate, followed by a crystallization step of the granules, thus ensuring that a small amount of final product is recycled to the prior crystallization step in order to prevent the attachment of granules to an inner crystallization device, which occurs due to local sintering in a high-temperature crystallization condition of continual process and also to further enhance the unit productivity during the mass production of crystalline layered sodium disilicate.</p>					